

Title (en)
SEMICONDUCTOR MATERIALS PREPARED FROM DITHIENYLVINYLENE COPOLYMERS

Title (de)
AUS DITHIENYLVINYLENCOPOLYMEREN HERGESTELLTE HALBLEITERMATERIALIEN

Title (fr)
MATÉRIAUX SEMI-CONDUCTEURS PRÉPARÉS À PARTIR DE COPOLYMÈRES DE DITHIÉNYLVINYLÈNE

Publication
EP 2379617 A2 20111026 (EN)

Application
EP 09795974 A 20091216

Priority

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- EP 09795974 A 20091216

Abstract (en)
[origin: WO2010079064A2] Disclosed are new semiconductor materials prepared from dithienylvinylene copolymers with aromatic or heteroaromatic p-conjugated systems. Such copolymers, with little or no post-deposition heat treatment, can exhibit high charge carrier mobility and/or good current modulation characteristics. In addition, the polymers of the present teachings can possess certain processing advantages such as improved solution-processability and low annealing temperature.

IPC 8 full level
C08G 61/12 (2006.01)

CPC (source: EP KR US)
C08F 228/06 (2013.01 - US); **C08G 61/126** (2013.01 - EP KR US); **C08K 3/01** (2018.01 - EP US); **C08K 5/0008** (2013.01 - EP US); **C09K 11/06** (2013.01 - EP US); **H10K 10/466** (2023.02 - KR); **H10K 10/484** (2023.02 - KR); **H10K 85/113** (2023.02 - EP KR US); **H10K 85/151** (2023.02 - EP KR US); **C08G 2261/124** (2013.01 - EP KR US); **C08G 2261/18** (2013.01 - EP KR US); **C08G 2261/3223** (2013.01 - EP US); **C08G 2261/3327** (2013.01 - EP US); **C08G 2261/344** (2013.01 - EP KR US); **C08G 2261/364** (2013.01 - EP US); **C08G 2261/414** (2013.01 - EP US); **C08G 2261/512** (2013.01 - EP US); **C08G 2261/5222** (2013.01 - EP US); **C08G 2261/91** (2013.01 - EP US); **C08G 2261/92** (2013.01 - EP US); **C09K 2211/1416** (2013.01 - EP US); **C09K 2211/1425** (2013.01 - EP US); **C09K 2211/1458** (2013.01 - EP US); **C09K 2211/1491** (2013.01 - EP US); **H10K 10/466** (2023.02 - EP US); **H10K 10/484** (2023.02 - EP US); **H10K 30/00** (2023.02 - US); **H10K 30/50** (2023.02 - EP KR); **H10K 2102/00** (2023.02 - KR); **Y02E 10/549** (2013.01 - EP KR US); **Y02P 70/50** (2015.11 - EP US)

Designated contracting state (EPC)
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